Page 1 (No. of pages: 2)
MINISTRY OF SUPPLY (D.C.D.)

VALVE ELECTRONIC (VT75A)

CVI576

Specification MAP/CV1576/Issue 7 SECURITY Dated 24.7.47. Specification Valve To be read in conjunction with K1001 RESTRICTED RESTRICTED ignoring clause 5.2. Indicates a change TYPE OF VALVE : Output tetrode MARKING (Pentode characteristic) : Indirectly heated CATHODE See K1001/4 : Glass-unmetallised ENVELOPE : KT44T PROTOTYPE BASE RATING Note B**7** Heater Voltage 4.0 Electrode Pin (A) Heater Current 2.0 1 No connection Normal Continuous Opera-2 Control grid tion 34 Beam forming plates Max. Anode Voltage Heater (V) 400 5 300 Heater Max. Screen Voltage Cathode 10.01 Max. Anode Dissipation (W) Max. Screen Dissipation(W) 3.0 7 Screen grid T.C. Anode 6.25 Mutual Conductance (mA/V) A Pulse Working The beam forming plates may be internally connected to cathode in which case Max. Anode Supply (kV) 1.0 there would be no connection to Pin 3. Voltage Max. Screen Supply (kV) 1.0 Voltage TOP CAP Max. Peak Anode Vol-(kV) 10.0 tage See K1001/AI/D5.1 NOTE DIMENSIONS A. Va = 250, Vg2 = 250, Ia = 85 mA. See K1001/AI/D1. Min. Max. Dimension 144 152 (mm) A В (mm) 57

CVI576

To be performed in addition to those applicable in K1001.

	<b></b>			~ 3114				Limits No.		
	Test Comditions					Test		Min.	Max.	Tested
Before the following tests are made, the valve is to be run for a period of 5 minutes with Vf = 4.0, Va = Vg2 = 250, Ia = 85 mA. The beam forming plates are to be connected to the cathode during this warming period and during the following tests.										
	٧f	Va	Vg2	Vg1	Ia (mA)		*****	1	<u> </u>	4007
a	4.0	0	0	Ú	0	Ih	(A)	1.8	2.2	100% or S
b	4.0	250	250	-	85	Reverse Ig1	(μA)	-	2.5	100%
С	The valve shall be pr cessed so that it will withstand the following conditions for one minute without flashing occurring (See Note 1)									
	4.2	See Note 2	800	Not more posi- tive than -200	-					100% See Note
đ	4.2	500	800	+50 See Note 3	-	(1) Ia (2) Ig2	(A) (mA)	1.6 To be than 2 of and current readir (d.1)	20% ode nt	100% 100%
е	4.2	500	600	+50 See Note 3	-	Ig1		To be	posi	100%
f	4.2	1kV	1 kV	-200	-	Ia	(mA)	-	1.0	100%
g										1% (10)

## NOTES

- 1. The processing shall be carried out in an approved apparatus and once the conditions specified in clause 'c' have been met, the test conditions need not be repeated for acceptance testing.
- 2. Pulse of approximately half sine wave shape, 9 kV. (approx.) instantaneous peak, superimposed on 1 kV. D.C. and 2  $\mu$ secs. half period to be applied 750  $\pm$  250 times per second.
- 3. This voltage to be applied as an intermittent pulse of, say, 10  $\mu$ secs. duration. Measurements to be made when grid is 50 volts positive.